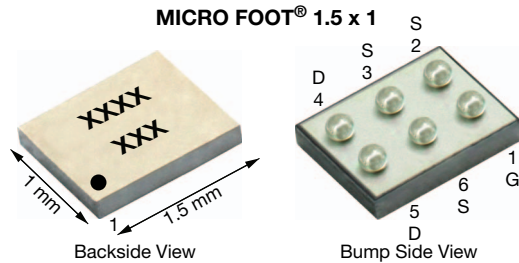


P-Channel 30 V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω) MAX.	I _D (A) ^d	Q _g (TYP.)
-30	0.053 at V _{GS} = -4.5 V	-13	16.3 nC
	0.071 at V _{GS} = -2.5 V	-11	
	0.120 at V _{GS} = -2 V	-5	



Marking Code: xxxx = 8497

xxx = Date / lot traceability code

Ordering Information:

Si8497DB-T2-E1 (Lead (Pb)-free and halogen-free)

FEATURES

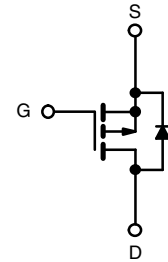
- TrenchFET[®] power MOSFET
- Ultra-small 1.5 mm x 1 mm maximum outline
- Ultra-thin 0.59 mm maximum height
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Low on-resistance load switch, charger switch, OVP switch and battery switch for portable devices
 - Low power consumption
 - Increased battery life
 - Space savings on PCB



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V _{DS}	-30	V
Gate-Source Voltage	V _{GS}	± 12	
Continuous Drain Current (T _J = 150 °C)	I _D	T _C = 25 °C	-13
		T _C = 70 °C	-10
		T _A = 25 °C	-5.9 ^{a, b}
		T _A = 70 °C	-4.7 ^{a, b}
Pulsed Drain Current (t = 300 μs)	I _{DM}	-20	A
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	
		T _A = 25 °C	-2.3 ^{a, b}
Maximum Power Dissipation	P _D	T _C = 25 °C	13
		T _C = 70 °C	8.4
		T _A = 25 °C	2.77 ^{a, b}
		T _A = 70 °C	1.77 ^{a, b}
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 150	°C
Package Reflow Conditions ^c	IR/Convection	260	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT
Maximum Junction-to-Ambient ^{a, e}	R _{thJA}	37	45	°C/W
Maximum Junction-to-Case (Drain) ^f	R _{thJC}	7	9.5	

Notes

- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- Refer to IPC/JEDEC[®] (J-STD-020), no manual or hand soldering.
- Based on T_C = 25 °C.
- Maximum under steady state conditions is 85 °C/W.
- Case is defined as top surface of the package.



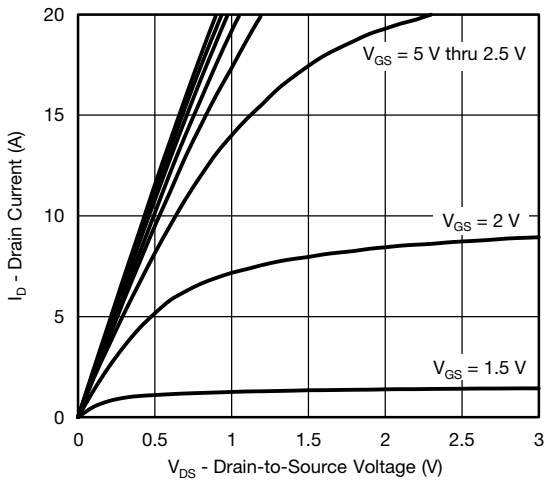
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0, I_D = -250\text{ }\mu\text{A}$	-30	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$	-	-29	-	mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		-	3.1	-	
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.5	-	-1.1	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$	-	-	-1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 70\text{ }^\circ\text{C}$	-	-	-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	-5	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -1.5\text{ A}$	-	0.043	0.053	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -1\text{ A}$	-	0.058	0.071	
		$V_{GS} = -2\text{ V}, I_D = -0.5\text{ A}$	-	0.075	0.120	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -1.5\text{ A}$	-	10	-	S
Dynamic ^b						
Input Capacitance	C_{ISS}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	1320	-	pF
Output Capacitance	C_{OSS}		-	121	-	
Reverse Transfer Capacitance	C_{RSS}		-	102	-	
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -1.5\text{ A}$	-	32.6	49	nC
		$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.5\text{ A}$	-	16.3	25	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -1.5\text{ A}$	-	2.5	-	
Gate-Drain Charge	Q_{gd}		-	4.9	-	
Gate Resistance	R_g	$V_{GS} = -0.1\text{ V}, f = 1\text{ MHz}$	-	8	-	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1.5\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$	-	17	35	ns
Rise Time	t_r		-	15	30	
Turn-Off Delay Time	$t_{d(off)}$		-	60	120	
Fall Time	t_f		-	25	50	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 10\text{ }\Omega$ $I_D \cong -1.5\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$	-	50	100	
Rise Time	t_r		-	10	20	
Turn-Off Delay Time	$t_{d(off)}$		-	75	150	
Fall Time	t_f		-	22	45	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$	-	-	-15	A
Pulse Diode Forward Current	I_{SM}		-	-	-20	
Body Diode Voltage	V_{SD}	$I_S = -1.5\text{ A}, V_{GS} = 0$	-	-0.73	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -1.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$	-	21	40	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	7	15	nC
Reverse Recovery Fall Time	t_a		-	8	-	ns
Reverse Recovery Rise Time	t_b		-	13	-	

Notes

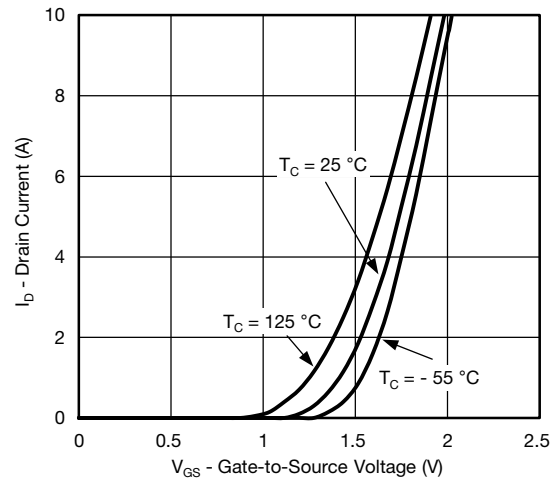
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

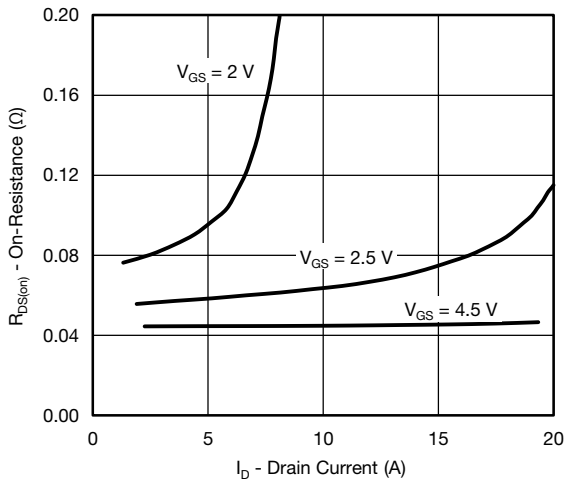
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



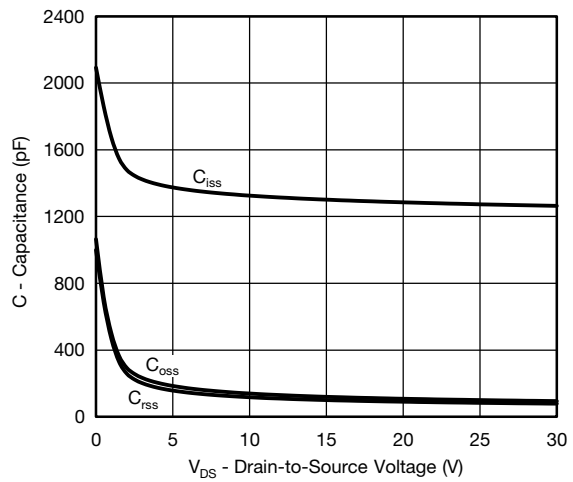
Output Characteristics



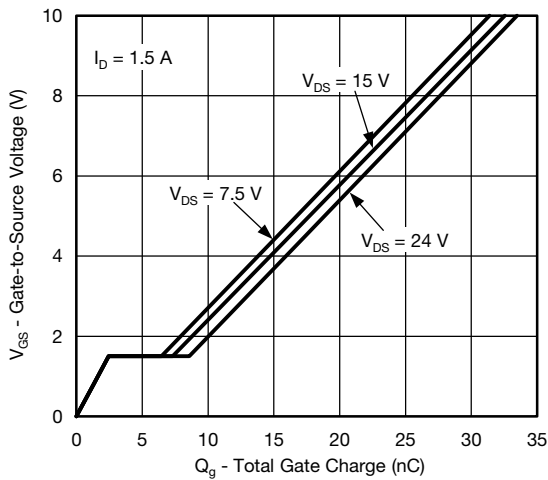
Transfer Characteristics



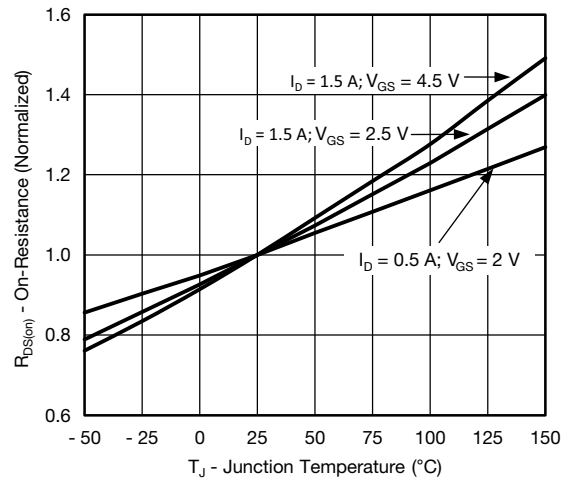
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

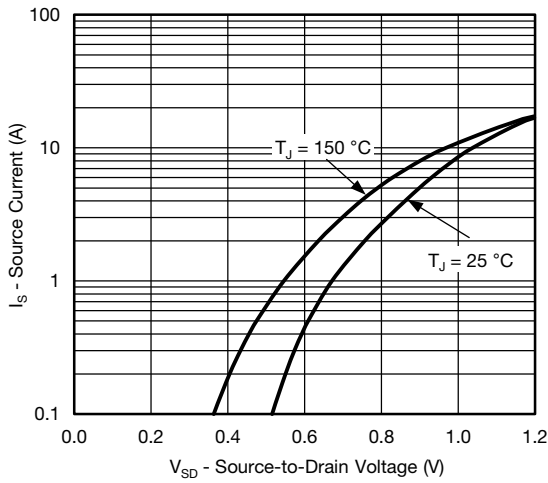


Gate Charge

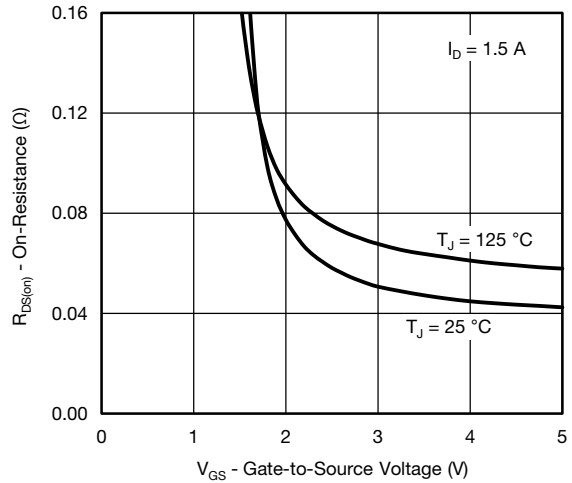


On-Resistance vs. Junction Temperature

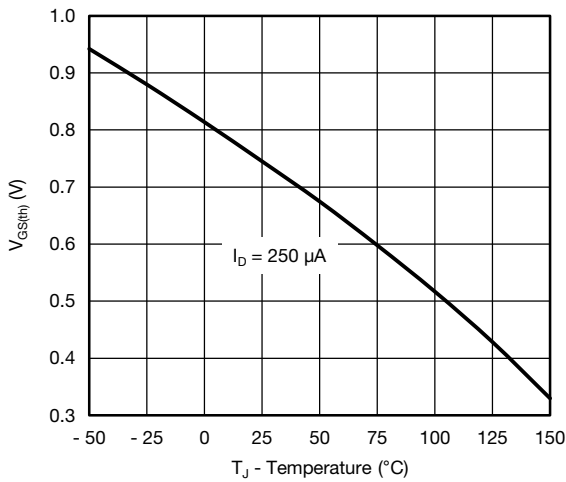
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



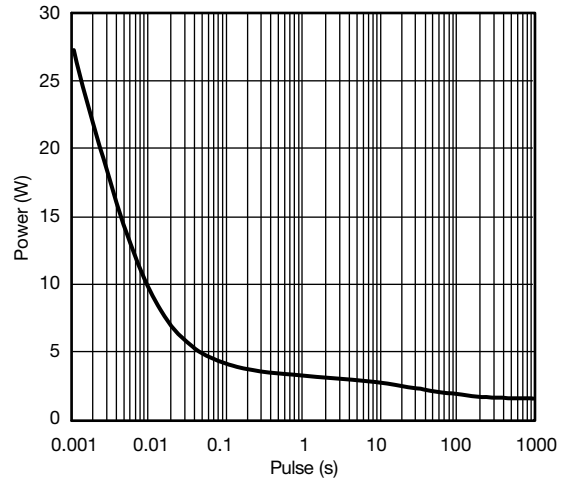
Source-Drain Diode Forward Voltage



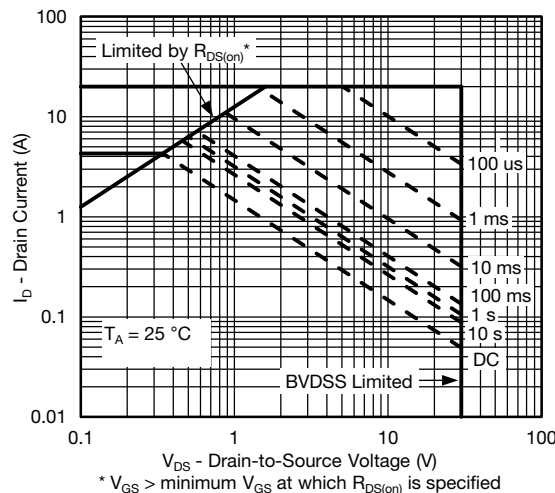
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



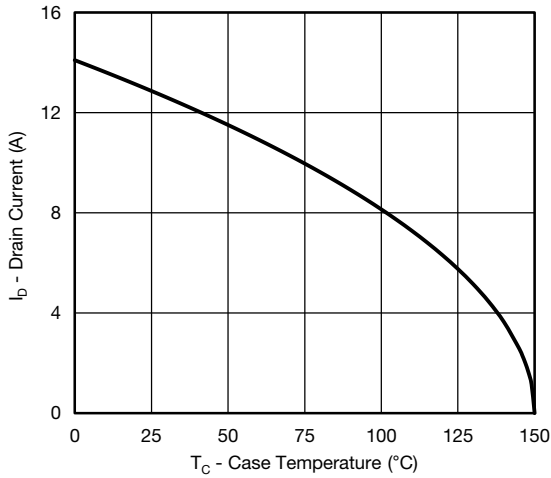
Single Pulse Power, Junction-to-Ambient



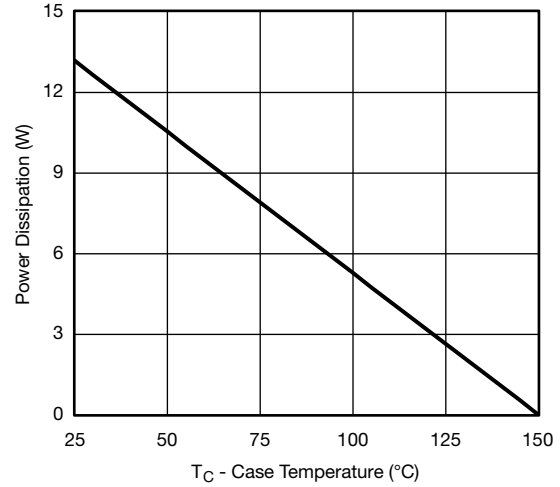
Safe Operating Area, Junction-to-Ambient



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



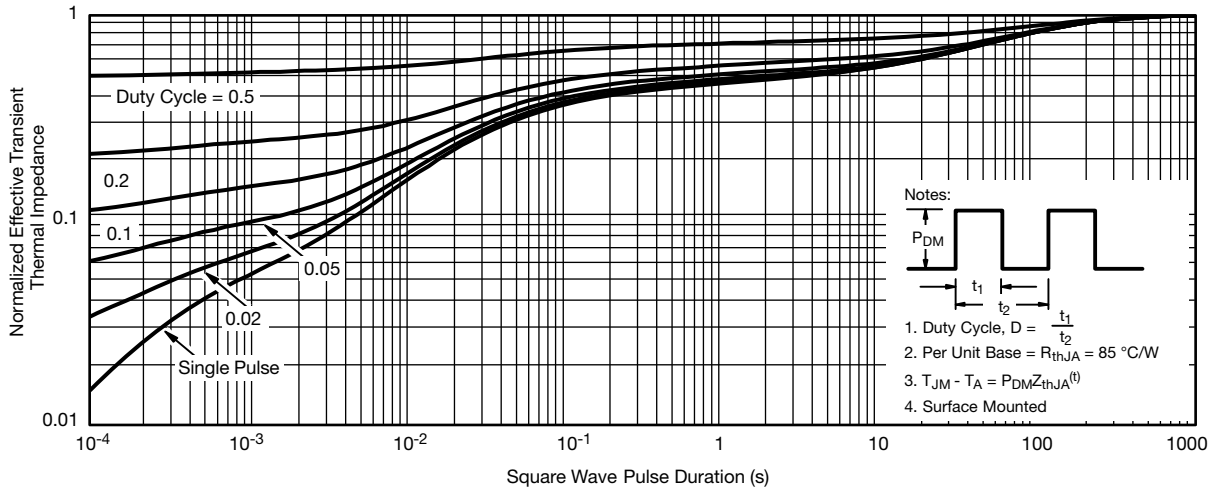
Current Derating*



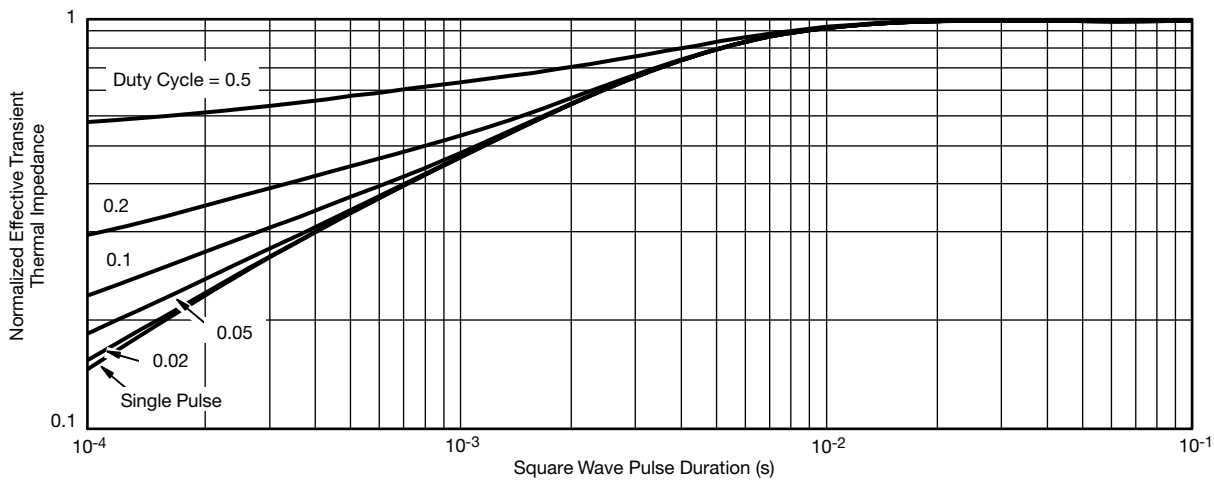
Power Derating

* The power dissipation P_D is based on T_{J(max.)} = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



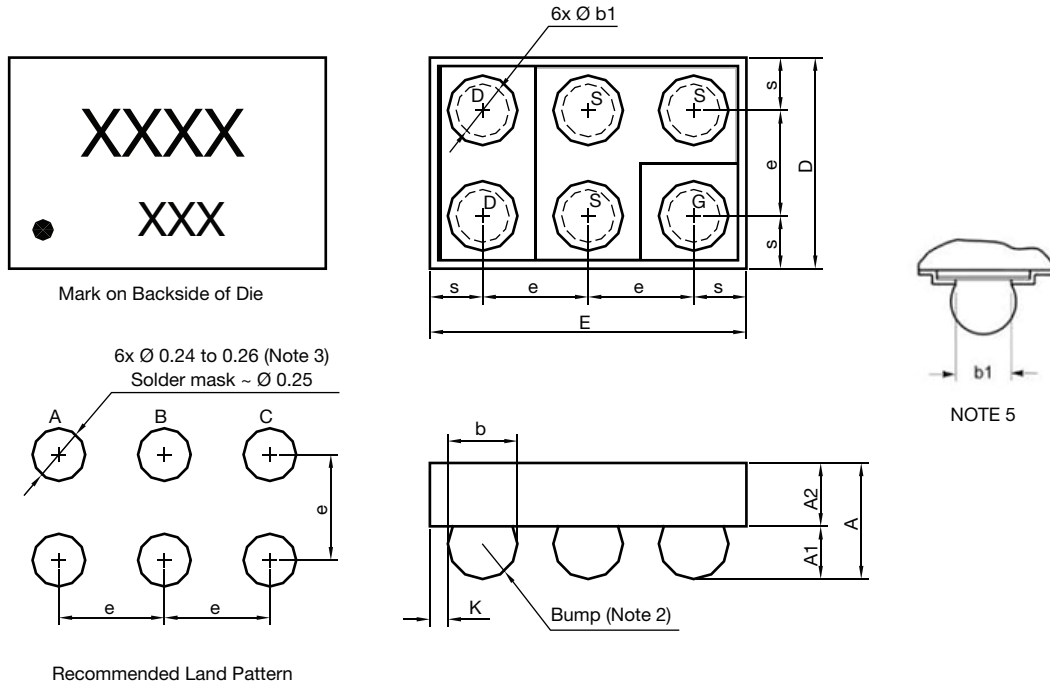
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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MICRO FOOT[®]: 6-Bump (1.5 mm x 1 mm, 0.5 mm Pitch, 0.250 mm Bump Height)


Notes

(unless otherwise specified)

1. Six (6) solder bumps are 95.5/3.8/0.7 Sn/Ag/Cu.
2. Backside surface is coated with a Ti/Ni/Ag layer.
3. Non-solder mask defined copper landing pad.
4. Laser marks on the silicon die back.
5. "b1" is the diameter of the solderable substrate surface, defined by an opening in the solder resist layer solder mask defined.
6. • is the location of pin 1

DIM.	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.510	0.575	0.590	0.0201	0.0226	0.0232
A ₁	0.220	0.250	0.280	0.0087	0.0098	0.0110
A ₂	0.290	0.300	0.310	0.0114	0.0118	0.0122
b	0.297	0.330	0.363	0.0116	0.0129	0.0143
b1		0.250			0.0098	
e		0.500			0.0197	
s	0.210	0.230	0.250	0.0082	0.0090	0.0098
D	0.920	0.960	1.000	0.0362	0.0378	0.0394
E	1.420	1.460	1.500	0.0559	0.0575	0.0591
K	0.028	0.065	0.102	0.0011	0.0025	0.0040

Note

- Use millimeters as the primary measurement.

 ECN: T15-0140-Rev. A, 20-Apr-15
 DWG: 6035



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